HD74HC620/HD74HC623

Octal Bus Transceivers (with inverted 3-state outputs)
Octal Bus Transceivers (with 3-state outputs)

HITACHI

Description

This octal bus transceiver is designed for asynchronous two-way communication between data buses. The control fuction implementation allows for maximum flexibility in timing.

This device allows data transmission from the A bus to the B bus or from the B bus to the A bus depending upon the logic levels at the enable inputs ($\overline{GBA}$ and GAB).

The enable inputs can be used to disable the device so that the buses are effectively isolated.

The dual-enable configuration gives these devices the capability to store data by simultaneous enabling of $\overline{GBA}$ and GAB. Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of bus lines are at high impedance, both sets of bus lines (16 in all) will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical for the HD74HC623 or coplementary for the HD74HC620.

Features

- High Speed Operation: t_{pd} (Bus to Bus) = 12 ns typ (C_L = 50 pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: V_{CC} = 2 to 6 V
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 µA max (Ta = 25°C)

Function Table

Enable Inputs		Operation	
$\overline{GBA}$	GAB	HD74HC620	HD74HC623
L	L	$\overline{B}$ data to A bus	B data to A bus
H	H	$\overline{A}$ data to B bus	A data to B bus
H	L	Isolation	Isolation
L	H	$\overline{B}$ data to A bus, $\overline{A}$ data to B bus	B data to A bus, A data to B bus

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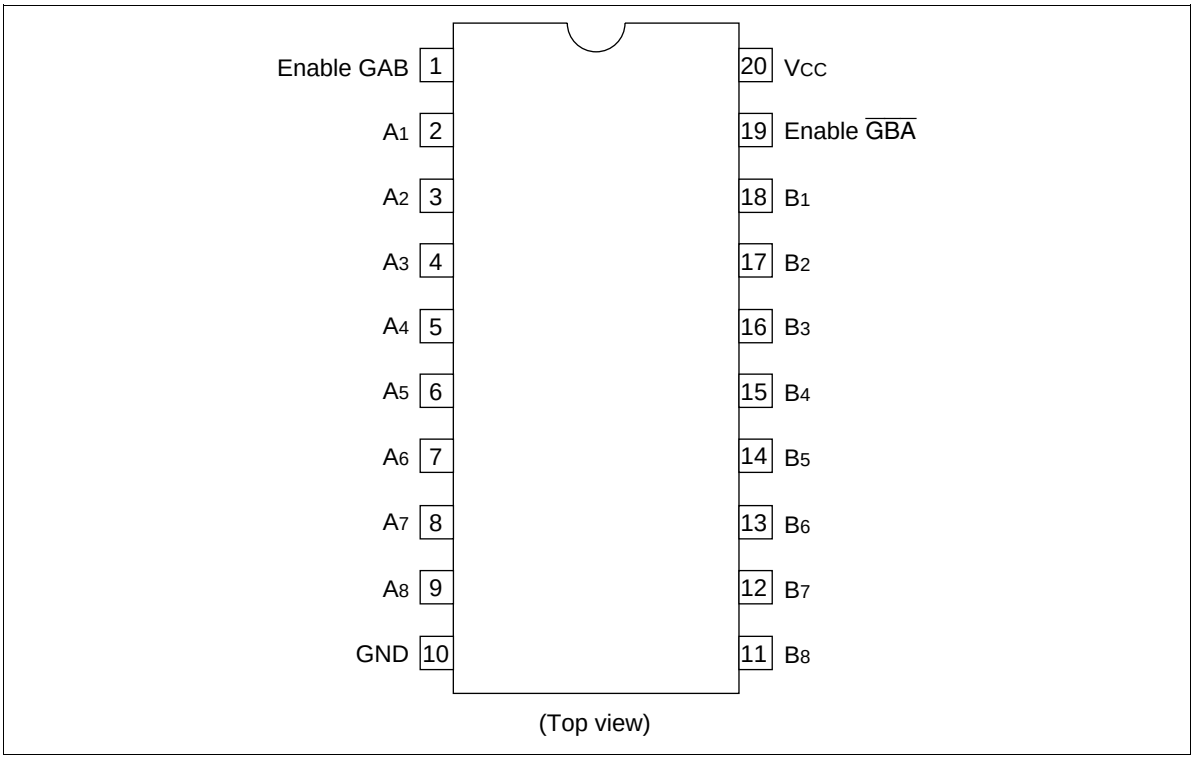
Pin Arrangement



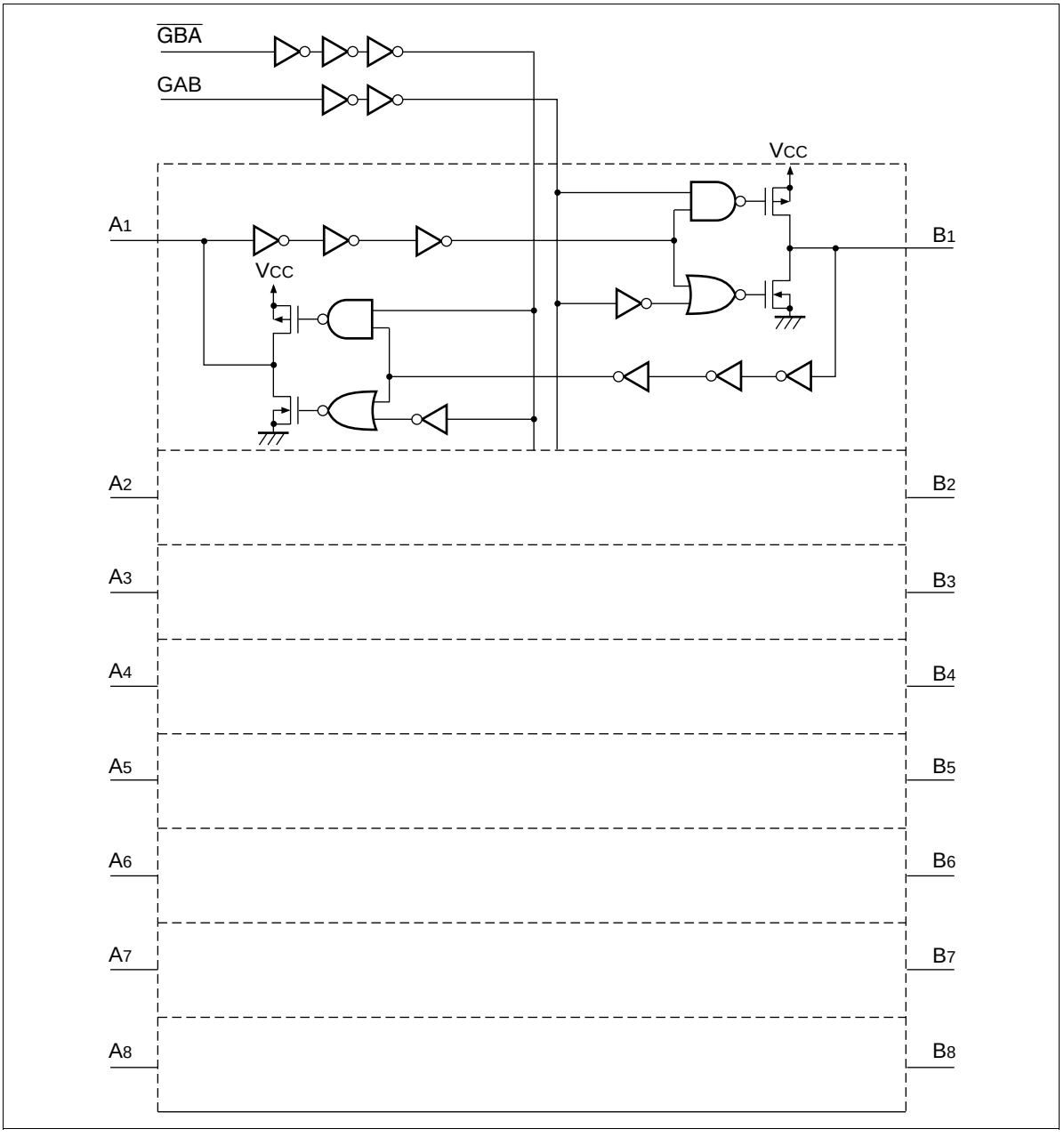
(Top view)

Absolute Maximum Ratings

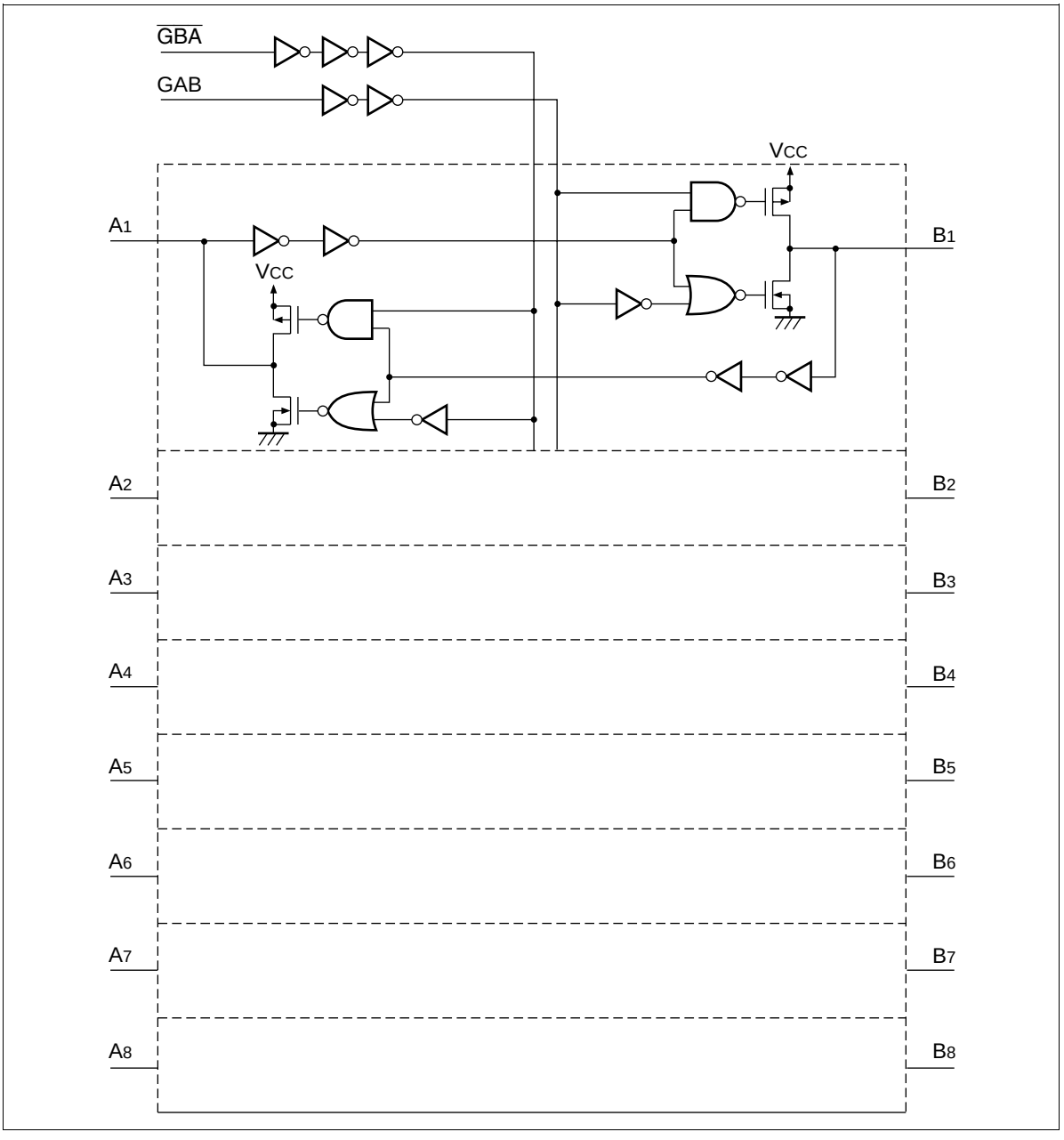
Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} + 0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} + 0.5	V
Output current	I_{OUT}	±35	mA
DC current drain per V_{CC} GND	I_{CC}, I_{GND}	±75	mA
DC input diode current	I_{IK}	±20	mA
DC output diode current	I_{OK}	±20	mA
Power Dissipation per package	P_T	500	mW
Storage temperature	Tstg	–65 to +150	°C

Block Diagram

HD74HC620



HD74HC623



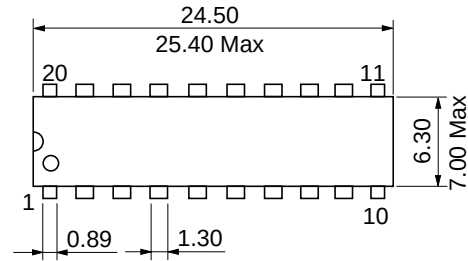
DC Characteristics

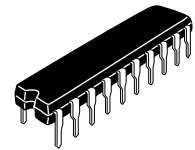
Item	Symbol	V_{CC} (V)	Ta = 25°C Min	Typ	Max	Ta = –40 to +85°C Min	Max	Unit	Test Conditions	
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V_{IH} or V_{IL}	I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I_{OH} = –6 mA
		6.0	5.68	—	—	5.63	—			I_{OH} = –7.8 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V_{IH} or V_{IL}	I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I_{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I_{OL} = 7.8 mA
Off-state output current	I_{OZ}	6.0	—	—	±0.5	—	±5.0	µA	Vin = V_{IH} or V_{IL}, Vout = V_{CC} or GND	
Input current	Iin	6.0	—	—	±0.1	—	±1.0	µA	Vin = V_{CC} or GND	
Quiescent supply current	I_{CC}	6.0	—	—	4.0	—	40	µA	Vin = V_{CC} or GND, Iout = 0 µA	

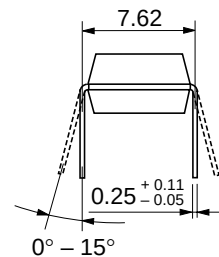
AC Characteristics (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

			Ta = 25°C			Ta = –40 to +85°C			
Item	**Symbol**	**V_{cc} (V)**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**
Propagation delay time	t_{PLH}	2.0	—	—	100	—	125	ns	
	t_{PHL}	4.5	—	12	20	—	25		
		6.0	—	—	17	—	21		
Output enable time	t_{ZH}	2.0	—	—	150	—	190	ns	
	t_{ZL}	4.5	—	12	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{HZ}	2.0	—	—	150	—	190	ns	
	t_{LZ}	4.5	—	16	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	Cin	—	—	5	10	—	10	pF	

Unit: mm

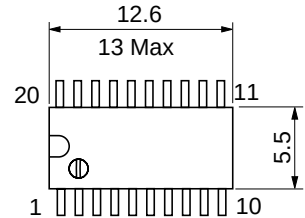


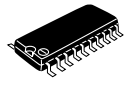


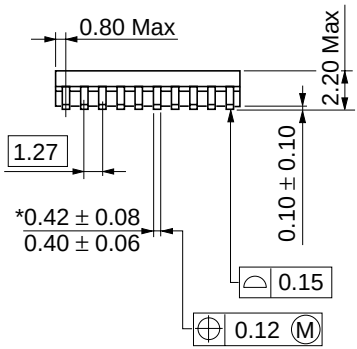


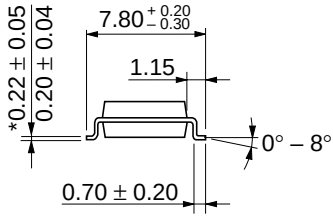
Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g

Unit: mm





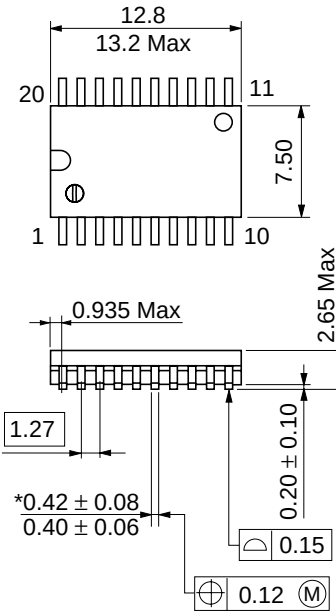


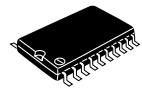


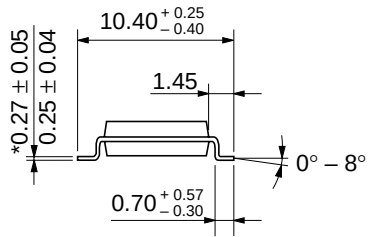
*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g

Unit: mm







*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

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